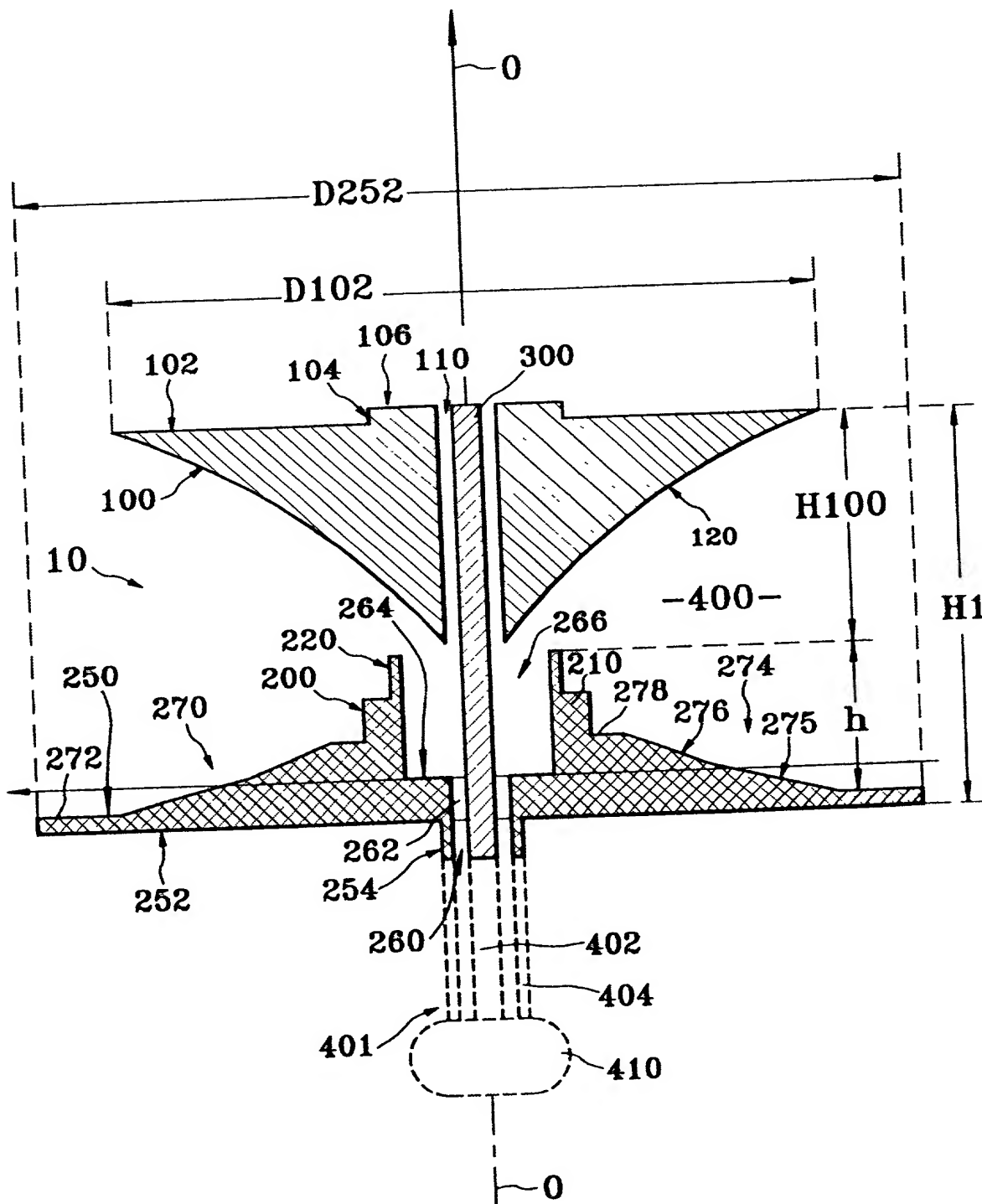


FIG. 1



Generator

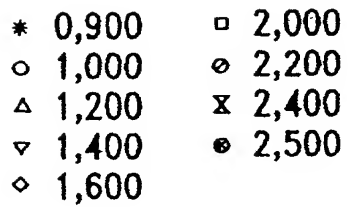
[illegible]

FIG. 4

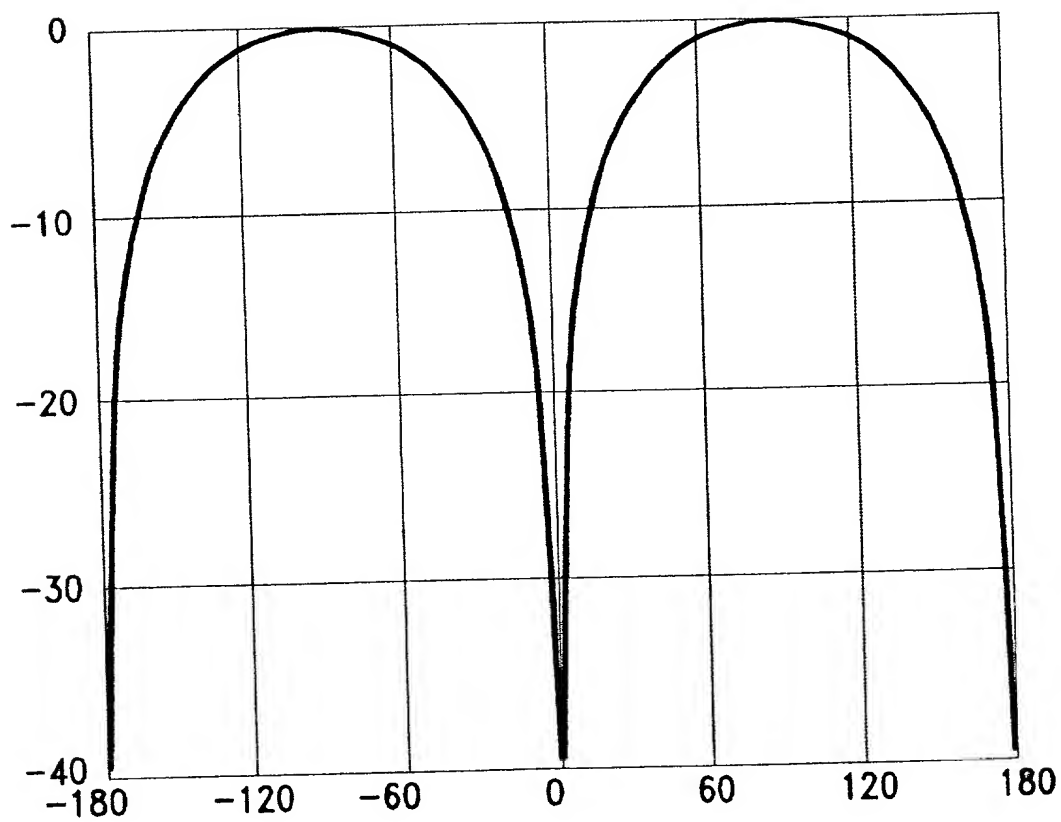
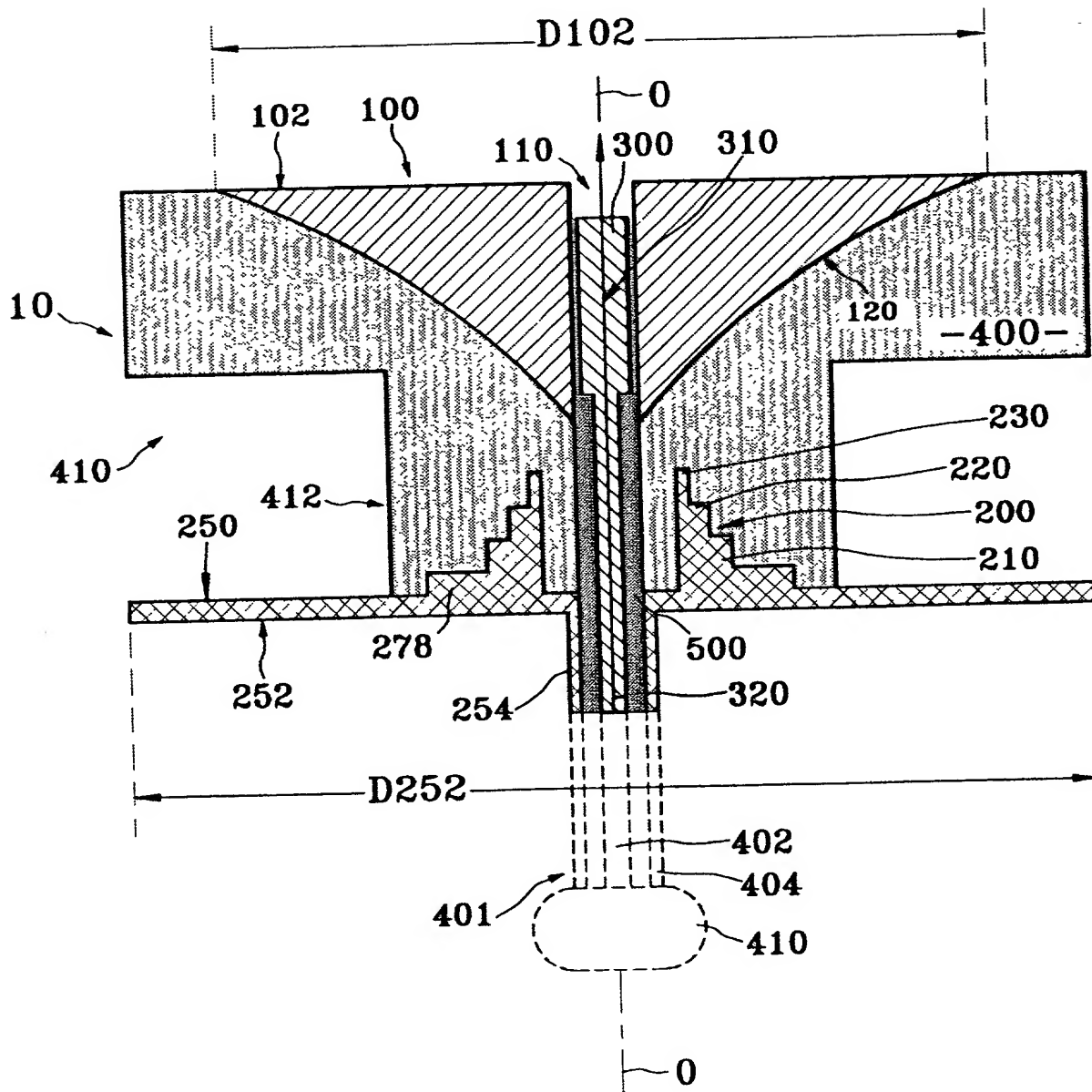


FIG. 5



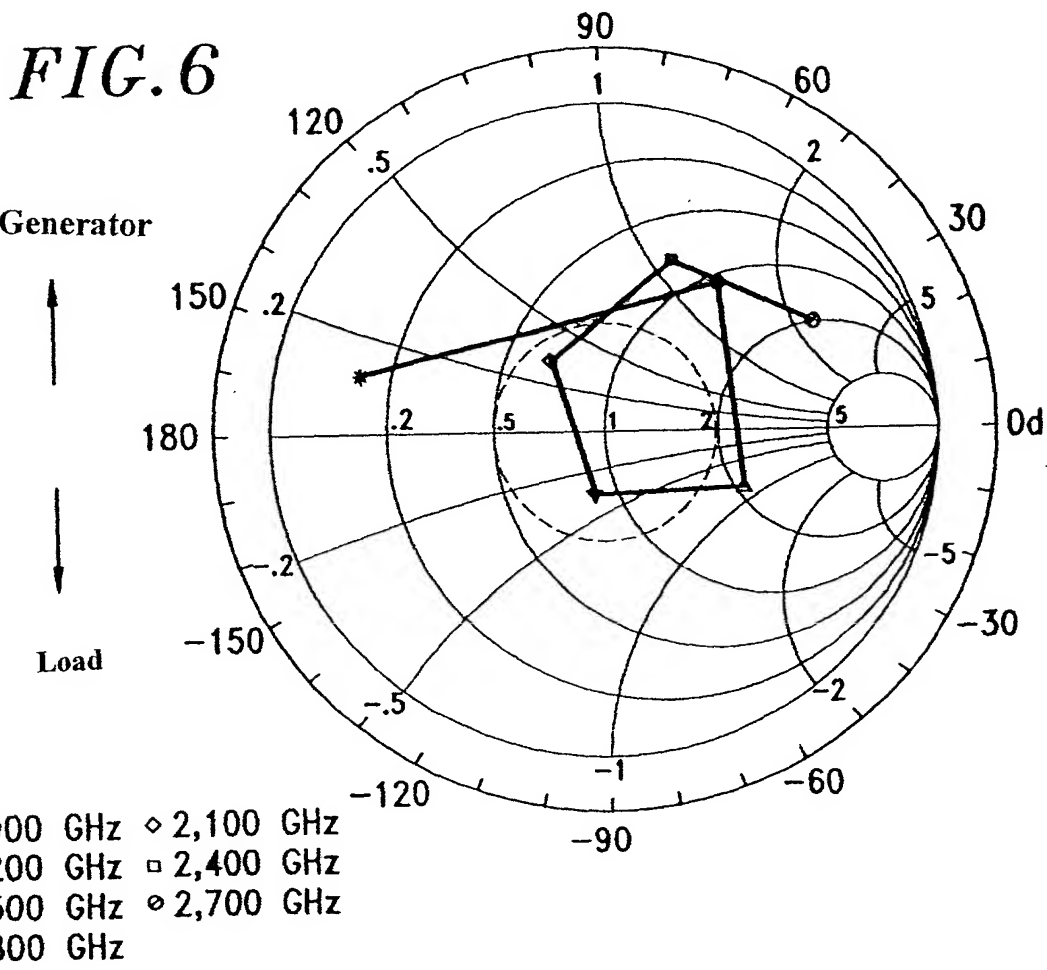


FIG. 7

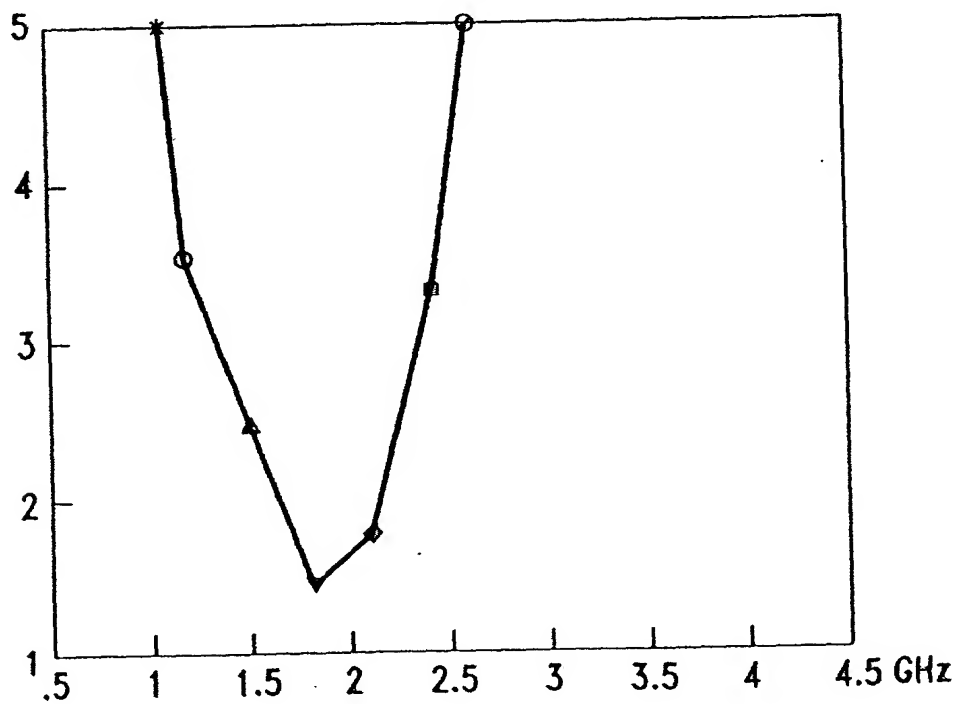


FIG. 1 is a cross-sectional view of a semiconductor device 100. It shows a substrate 102 with a curved top surface 110. A layer 120 is formed on the substrate 102. A gate structure 200 is formed on the substrate 102, with a gate dielectric layer 210, a gate conductive layer 220, and a gate insulating layer 230. A source/drain region 250 is formed in the substrate 102, with a source/drain conductive layer 252 and a source/drain insulating layer 255. A contact layer 278 is formed on the source/drain conductive layer 252. A contact pad 280 is formed on the contact layer 278. A first electrode 300 is formed on the contact pad 280, with a first electrode conductive layer 302 and a first electrode insulating layer 304. A second electrode 320 is formed on the first electrode 300, with a second electrode conductive layer 322 and a second electrode insulating layer 324. A third electrode 340 is formed on the second electrode 320, with a third electrode conductive layer 342 and a third electrode insulating layer 344. A fourth electrode 360 is formed on the third electrode 340, with a fourth electrode conductive layer 362 and a fourth electrode insulating layer 364. A fifth electrode 380 is formed on the fourth electrode 360, with a fifth electrode conductive layer 382 and a fifth electrode insulating layer 384. A sixth electrode 400 is formed on the fifth electrode 380, with a sixth electrode conductive layer 402 and a sixth electrode insulating layer 404.

FIG. 2 is a cross-sectional view of a semiconductor device 400. It shows a substrate 402 with a curved top surface 410. A layer 412 is formed on the substrate 402. A gate structure 420 is formed on the substrate 402, with a gate dielectric layer 422, a gate conductive layer 424, and a gate insulating layer 426. A source/drain region 430 is formed in the substrate 402, with a source/drain conductive layer 432 and a source/drain insulating layer 434. A contact layer 438 is formed on the source/drain conductive layer 432. A contact pad 440 is formed on the contact layer 438. A first electrode 450 is formed on the contact pad 440, with a first electrode conductive layer 452 and a first electrode insulating layer 454. A second electrode 470 is formed on the first electrode 450, with a second electrode conductive layer 472 and a second electrode insulating layer 474. A third electrode 490 is formed on the second electrode 470, with a third electrode conductive layer 492 and a third electrode insulating layer 494. A fourth electrode 510 is formed on the third electrode 490, with a fourth electrode conductive layer 512 and a fourth electrode insulating layer 514. A fifth electrode 530 is formed on the fourth electrode 510, with a fifth electrode conductive layer 532 and a fifth electrode insulating layer 534. A sixth electrode 550 is formed on the fifth electrode 530, with a sixth electrode conductive layer 552 and a sixth electrode insulating layer 554.

FIG. 9

